

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

TIG067SS — N-Channel IGBT

Light-Controlling Flash Applications

Features

- · Low-saturation voltage
- · Enhansment type
- · High speed switching

- · 4.0V drive
- · Built-in Gate-to-Emitter protection diode
- · Halogen free compliance

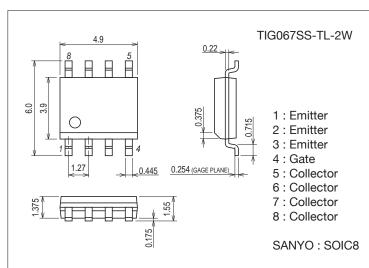
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Emitter Voltage (DC)	VCES		400	V
Collector-to-Emitter Voltage (Pulse)	VCESP	PW≤1ms	450	V
Gate-to-Emitter Voltage (DC)	VGES		±6	V
Gate-to-Emitter Voltage (Pulse)	VGESP	PW≤1ms	±8	V
Collector Current (Pulse)	ICP	C _M =600μF	150	Α
Maximum Collector-to-Emitter dv / dt	dv / dt	V _{CE} ≤320V, starting Tch=25°C	1500	V / μs
Allowable Power Dissipation	PD	When mounted on FR4 substrate (11,680mm ² ×1.6mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-40 to +150	°C

Package Dimensions

unit : mm (typ) 7072-002

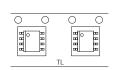


Product & Package Information

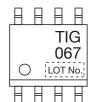
• Package : SOIC8

• JEITA, JEDEC : SC-87, SOT-96 • Minimum Packing Quantity : 2500 pcs./reel

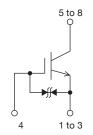
Packing Type: TL



Marking



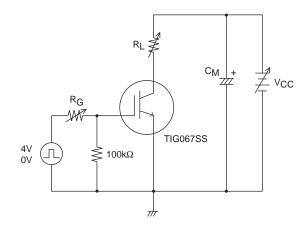
Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Syllibol	Conditions	min	typ	max	Uill
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC=2mA, VGE=0V	400			V
Collector-to-Emitter Cutoff Current	ICES	V _{CE} =320V, V _{GE} =0V			10	μA
Gate-to-Emitter Leakage Current	IGES	V _{GE} =±6V, V _{CE} =0V			±10	μA
Gate-to-Emitter Threshold Voltage	V _{GE} (off)	V _{CE} =10V, I _C =1mA	0.4		1.0	V
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=150A, VGE=4V		3.8	5	V
Input Capacitance	Cies			5100		pF
Output Capacitance	Coes	V _{CE} =10V, f=1MHz		59		pF
Reverse Transfer Capacitance	Cres			43		pF
Fall Time	tf	IC=150A, VCC=320V, Resistor load VGE=4V, RG=36Ω		270		ns

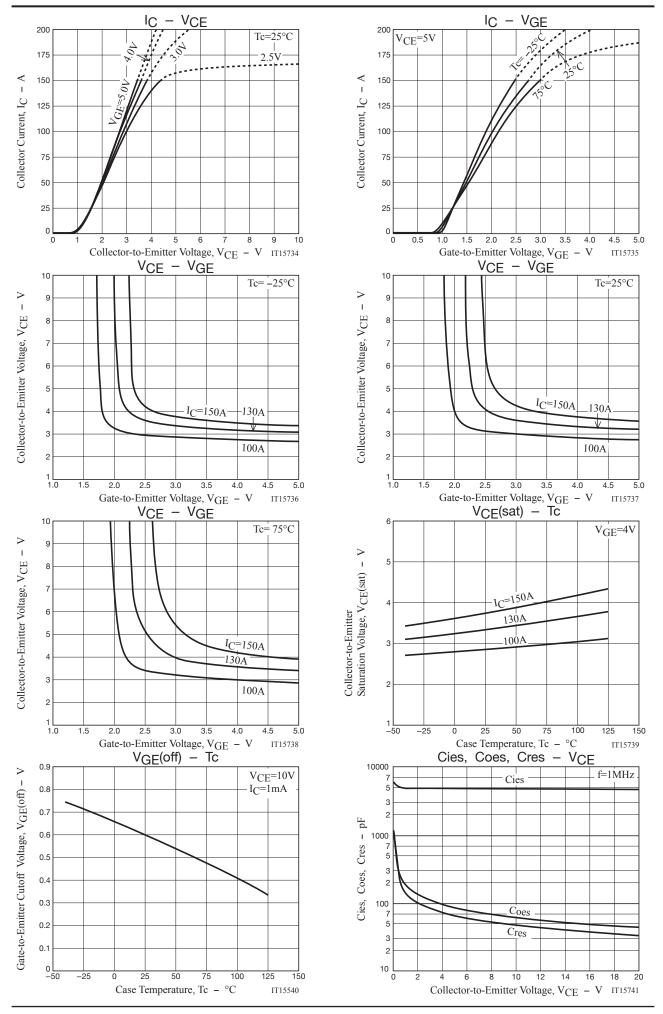
Fig1 Large Current R Load Switching Circuit

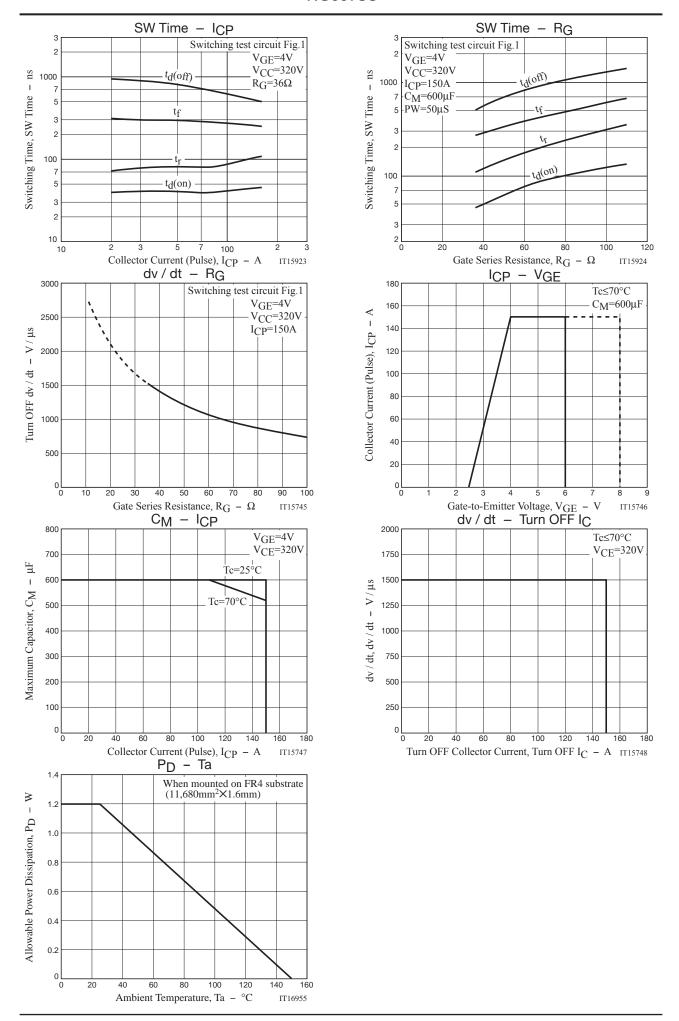


Note1. Gate Series Resistance $RG \ge 36\Omega$ is recommended for protection purpose at the time of turn OFF. However, if $dv / dt \le 1500 / \mu s$ is satisfied at customer's actual set evaluation, $RG < 36\Omega$ can also be used. Note2. The collector voltage gradient dv / dt must be smaller than $1500V / \mu s$ to protect the device when it is turned off.

Ordering Information

Device	Package	Shipping	memo	
TIG067SS-TL-2W	SOIC8	2,500pcs./reel	Pb Free and Halogen Free	



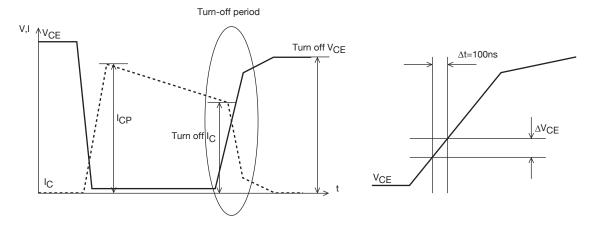


Definition of dv/dt

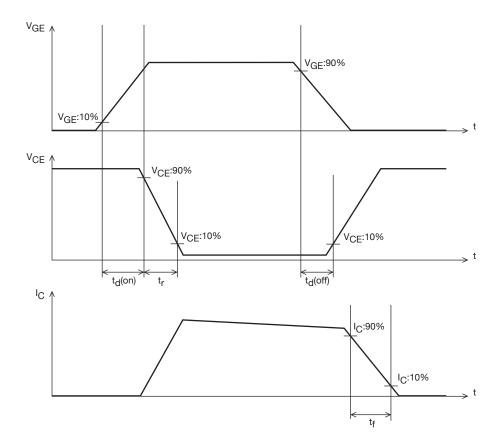
dv/dt is defined as the maximum slope of the below VCE curve during turn-off period. dv/dt= $\Delta VCE/\Delta t$ = $\Delta VCE/100 ns$

Overall waveform

Enlarged picture of turn-off period



Definition of Switching Time

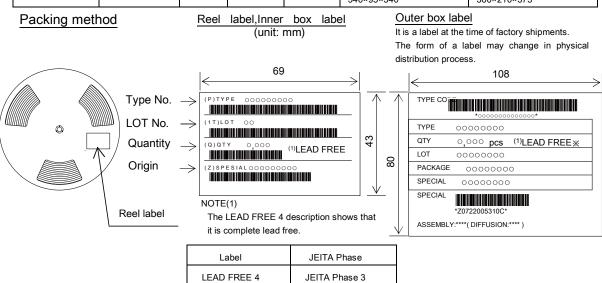


Taping Specification

TIG067SS-TL-2W

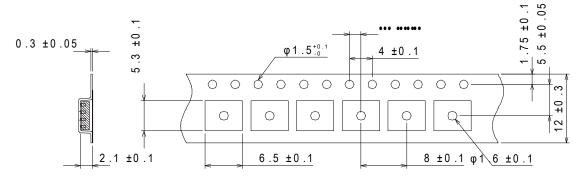
1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices			Packing format		
	Туре	contained (pcs)					
		Reel	Inner box	Outer box	Inner BOX W206-112	Outer BOX W207-124	
SOIC8	B202-101	2,500	12,500	25,000	5 reels contained	2 inner boxes contained	
					Dimensions :mm(external)	Dimensions :mm(external)	
					340×95×340	360×210×375	

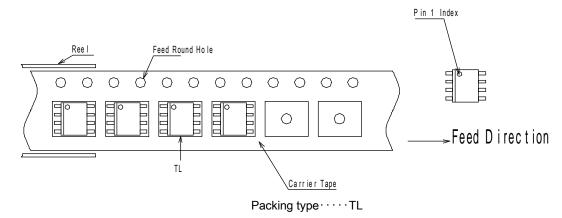


2. Taping configuration

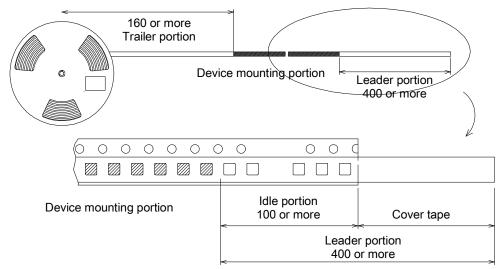
2-1. Carrier tape size (unit: mm)



2-2. Device placement direction



2-3. Leader portion and trailer portion (unit: mm)

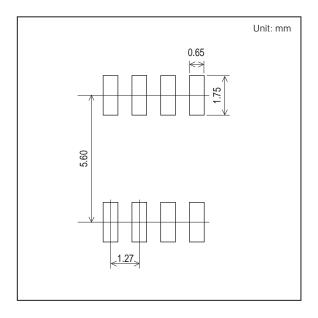


Outline Drawing

TIG067SS-TL-2W

Mass (g) Unit 0.082 mm 4.9481 8 7 6 5 1.271 2 3 4.4548.065 27551 1.271 **I:Lot Indication. *2:Lot Indication. Some products have no Lot indication.

Land Pattern Example



Note: TIG067SS has protection diode between gate and emitter but handling it requires sufficient care to be taken.

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